**Preferred Device** 

## **Sensitive Gate Triacs**

#### **Silicon Bidirectional Thyristors**

Designed for high volume, low cost, industrial and consumer applications such as motor control; process control; temperature, light and speed control.

#### **Features**

- Small Size Surface Mount DPAK Package
- Passivated Die for Reliability and Uniformity
- Four-Quadrant Triggering
- Blocking Voltage to 600 V
- On-State Current Rating of 4.0 A RMS at 93°C
- Low Level Triggering and Holding Characteristics
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B > 8000 V Machine Model, C > 400 V
- Pb-Free Packages are Available

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (T <sub>J</sub> = -40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open)	V <sub>DRM,</sub> V <sub>RRM</sub>	600	V
On–State RMS Current (Full Cycle Sine Wave, 60 Hz, T <sub>C</sub> = 93°C)	I <sub>T(RMS)</sub>	4.0	Α
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T <sub>J</sub> = 110°C)	I <sub>TSM</sub>	40	Α
Circuit Fusing Consideration (t = 8.3 msec)	I <sup>2</sup> t	6.6	A <sup>2</sup> sec
Peak Gate Power (Pulse Width ≤ 10 μsec, T <sub>C</sub> = 93°C)	P <sub>GM</sub>	2.0	W
Average Gate Power (t = 8.3 msec, T <sub>C</sub> = 93°C)	P <sub>G(AV)</sub>	1.0	W
Peak Gate Current (Pulse Width $\leq$ 20 $\mu$ sec, T <sub>C</sub> = 93°C)	I <sub>GM</sub>	4.0	Α
Peak Gate Voltage (Pulse Width $\leq$ 20 $\mu$ sec, T <sub>C</sub> = 93°C)	V <sub>GM</sub>	5.0	V
Operating Junction Temperature Range	TJ	-40 to 110	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

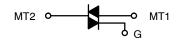
 V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the device are exceeded.



#### ON Semiconductor®

http://onsemi.com

# TRIACS 4.0 AMPERES RMS 600 VOLTS

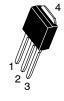


#### MARKING DIAGRAMS

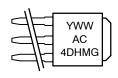


DPAK CASE 369C STYLE 6





DPAK-3 CASE 369D STYLE 6



Y = Year

WW = Work Week

AC4DHM = Device Code

G = Pb-Free Package

PIN ASSIGNMENT			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, – Junction-to-Case – Junction-to-Ambient – Junction-to-Ambient (Note 2)	$egin{array}{c} R_{ heta JC} \ R_{ heta JA} \end{array}$	3.5 88 80	°C/W
Maximum Lead Temperature for Soldering Purposes (Note 3)	TL	260	°C

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•			
Peak Repetitive Blocking Current $(V_D = Rated \ V_{DRM}, \ V_{RRM}; \ Gate \ Open) \\ T_J = 25^{\circ}C \\ T_J = 110^{\circ}C$	I <sub>DRM,</sub> I <sub>RRM</sub>		_ _	0.01 2.0	mA
ON CHARACTERISTICS					
Peak On-State Voltage (Note 4) - (I <sub>TM</sub> = ±6.0 A)	$V_{TM}$	-	1.3	1.6	V
Gate Trigger Current (Continuous dc) ( $V_D$ = 12 V, $R_L$ = 100 $\Omega$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	I <sub>GT</sub>	- - - -	1.8 2.1 2.4 4.2	5.0 5.0 5.0 10	mA
Gate Trigger Voltage (Continuous dc) ( $V_D$ = 12 V, $R_L$ = 100 $\Omega$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	V <sub>GT</sub>	0.5 0.5 0.5 0.5	0.62 0.57 0.65 0.74	1.3 1.3 1.3 1.3	V
Gate Non–Trigger Voltage (Continuous dc) – ( $V_D$ = 12 V, $R_L$ = 100 $\Omega$ , $T_J$ = 110°C) All Four Quadrants	$V_{GD}$	0.1	0.4	-	V
Holding Current (V <sub>D</sub> = 12 V, Gate Open, Initiating Current = ±200 mA)	I <sub>H</sub>	_	1.5	15	mA
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	ΙL	- - - -	1.75 5.2 2.1 2.2	10 10 10 10	mA
DYNAMIC CHARACTERISTICS					
Rate of Change of Commutating Current ( $V_D$ = 200 V, $I_{TM}$ = 1.8 A, Commutating dv/dt = 1.0 V/ $\mu$ sec, $T_J$ = 110°C, f = 250 Hz, CL = 5.0 $\mu$ fd, LL = 80 mH, RS = 56 $\Omega$ , CS = 0.03 $\mu$ fd) With snubber see Figure 11		-	3.0	-	A/ms
Critical Rate of Rise of Off–State Voltage $(V_D = 0.67 \text{ X Rated } V_{DRM}, \text{ Exponential Waveform,}$ Gate Open, $T_J = 110^{\circ}\text{C})$	dv/dt	20	-	-	V/μs

These ratings are applicable when surface mounted on the minimum pad sizes recommended.
 1/8" from case for 10 seconds.
 Pulse Test: Pulse Width ≤ 2.0 msec, Duty Cycle ≤ 2%.

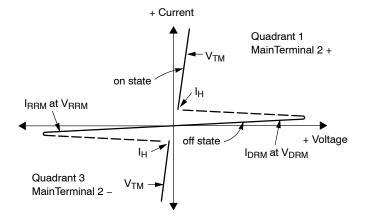
#### **ORDERING INFORMATION**

Device	Package Type	Package	Shipping <sup>†</sup>
MAC4DHM-001	DPAK-3	369D	75 Units / Rail
MAC4DHM-001G	DPAK-3 (Pb-Free)	369D	75 Units / Rail
MAC4DHMT4	DPAK	369C	2500 / Tape & Reel
MAC4DHMT4G	DPAK (Pb-Free)	369C	2500 / Tape & Reel

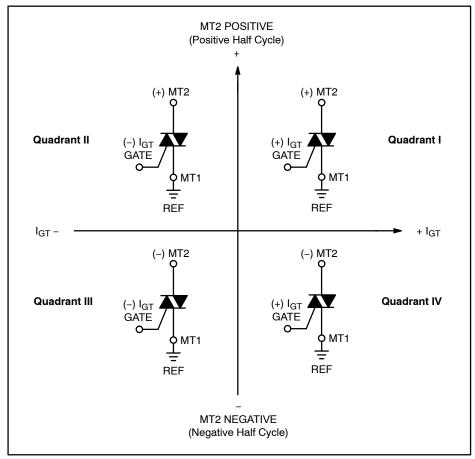
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off-State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off-State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Maximum On-State Voltage
I <sub>H</sub>	Holding Current



#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

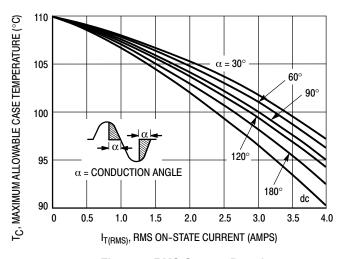


Figure 1. RMS Current Derating

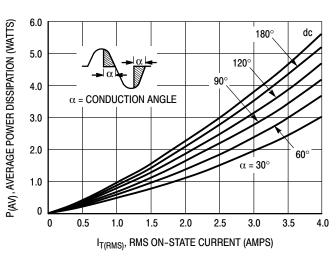


Figure 2. On-State Power Dissipation

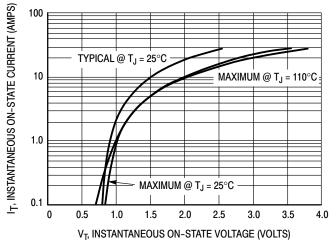
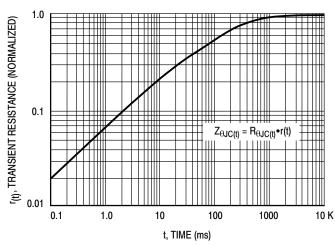


Figure 3. On-State Characteristics



**Figure 4. Transient Thermal Response** 

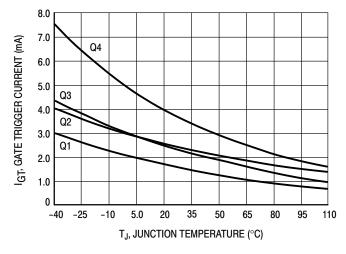


Figure 5. Typical Gate Trigger Current versus
Junction Temperature

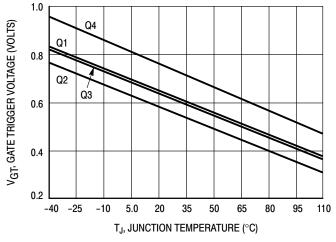
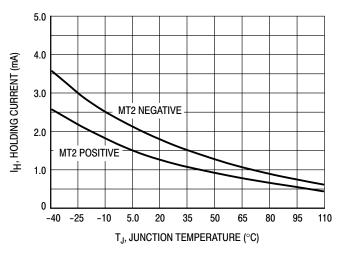


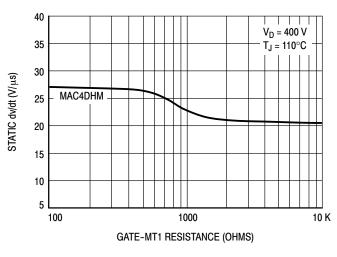
Figure 6. Typical Gate Trigger Voltage versus
Junction Temperature



12 10 IL, LATCHING CURRENT (mA) 8.0 Q2 6.0 4.0 Q4 2.0 0 -40 -25 -10 5.0 20 65 80 95 35 50 110 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 7. Typical Holding Current versus Junction Temperature

Figure 8. Typical Latching Current versus Junction Temperature



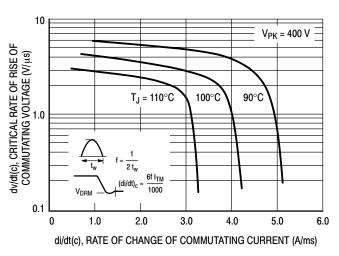
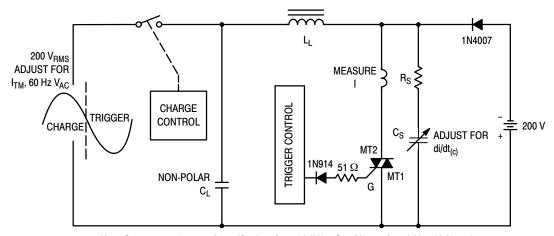


Figure 9. Minimum Exponential Static dv/dt versus Gate-MT1 Resistance

Figure 10. Typical Critical Rate of Rise of Commutating Voltage

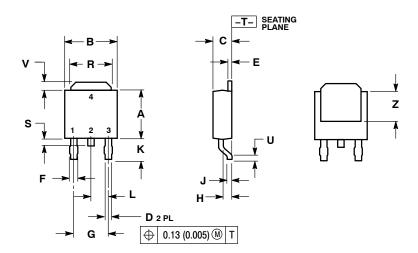


Note: Component values are for verification of rated (di/dt)<sub>c</sub>. See AN1048 for additional information.

Figure 11. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)<sub>c</sub>

#### **PACKAGE DIMENSIONS**

#### **DPAK** CASE 369C ISSUE O

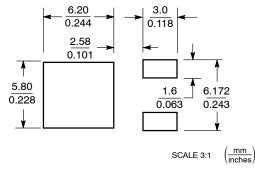


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.22
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58	BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090	BSC	2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020		0.51	
٧	0.035	0.050	0.89	1.27
Z	0.155		3.93	

STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2

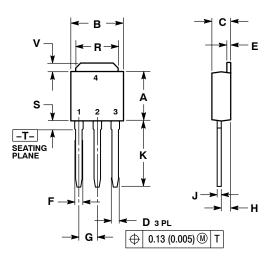
#### **SOLDERING FOOTPRINT\***

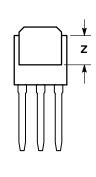


<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

DPAK-3 CASE 369D-01 ISSUE B





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- . CONTROLLING DIMENSION: INCH.

	INC	INCHES MILLIMET		IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.245	5.97	6.35	
В	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.027	0.035	0.69	0.88	
E	0.018	0.023	0.46	0.58	
F	0.037	0.045	0.94	1.14	
G	0.090	BSC	2.29	29 BSC	
Н	0.034	0.040	0.87 1.0		
J	0.018	0.023	0.46	0.58	
K	0.350	0.380	8.89	9.65	
R	0.180	0.215	4.45	5.45	
S	0.025	0.040	0.63	1.01	
٧	0.035	0.050	0.89	1.27	
z	0.155		3.93		

#### STYLE 6:

- PIN 1. MT1
  - 2. MT2
  - 3. GATE

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